

## Descriptions

This 60V 123A N-Channel MOSFET in a PDFN5×6 Plastic Package.

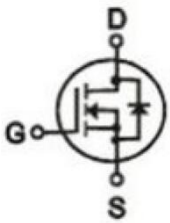
## Features

- Low  $R_{DS(ON)}$  to minimize conductive loss
- low gate charge for fast switching
- Low thermal resistance
- Halogen-free product.

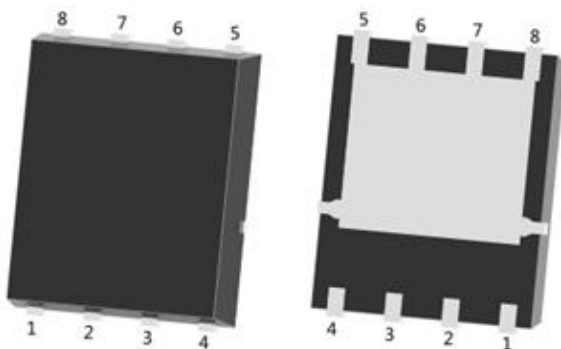
## Applications

- Battery management
- High frequency point-of-load synchronous buck converter for MB/NB/UMPC/VGA
- Networking DC-DC power system
- Load switch

## Equivalent Circuit



## Pinning



PIN1、2、3: S

PIN4: G

PIN5、6、7、8: D

Pin	极性
1	S
2	S
3	S
4	G
5	D
6	D
7	D
8	D

## Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=30V$ $R_L=1.5\ \Omega$ $R_{GEN}=3\ \Omega$		11		ns
Turn-On Rise Time	$t_r$			6		
Turn-Off Delay Time	$t_{d(off)}$			43		
Turn-Off Fall Time	$t_f$			2		

**Absolute Maximum Ratings(Ta=25°C)**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	V
Continuous Drain Current	I <sub>D</sub>	123	A
Pulsed Drain Current	I <sub>DM</sub>	253	A
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Power Dissipation	P <sub>D</sub> (T <sub>c</sub> =25°C)	83	W
Avalanche energy(L=0.5mH)	E <sub>AS</sub>	2000	mJ
Avalanche Current(L=0.5mH)	I <sub>AS</sub>	47	A
Junction and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C
Maximum Junction-to-Ambient	t ≤ 10s	20	°C/W
	Steady-State	50	
Maximum Junction-to-Case	Steady-State	1.5	

**Electrical Characteristics(Ta=25°C)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250uA, V <sub>GS</sub> =0V	60	77		V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1.0	uA
Gate-Body leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.6	2.5	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A		2.8	3	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A		3.8	5	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.64	1	V
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V V <sub>GS</sub> =0V f=1.0MHz		3710		pF
Output Capacitance	C <sub>oss</sub>			2100		
Reverse Transfer Capacitance	C <sub>rss</sub>			230		
Gate resistance	R <sub>g</sub>	V <sub>GS</sub> =0V V <sub>DS</sub> =0V f=1MHz		2.3		Ω
Total Gate Charge	Q <sub>g(10V)</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, I <sub>D</sub> =20A		51		nC
Total Gate Charge	Q <sub>g(4.5V)</sub>			25		
Gate Source Charge	Q <sub>gs</sub>			10		
Gate Drain Charge	Q <sub>gd</sub>			8.5		

Electrical Characteristic Curve

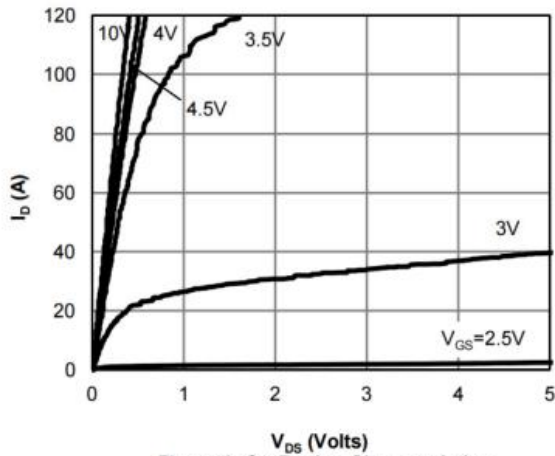


Figure 1: On-Region Characteristics

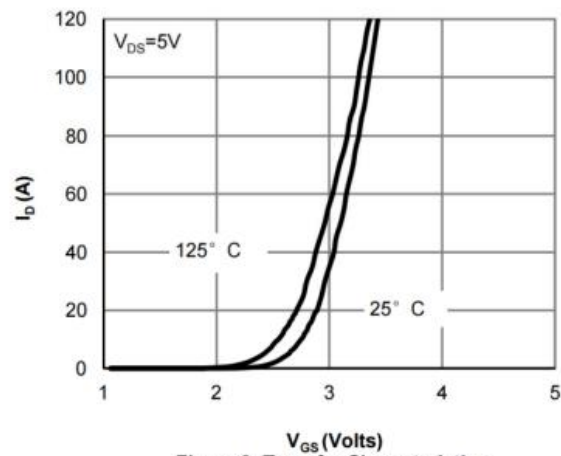


Figure 2: Transfer Characteristics

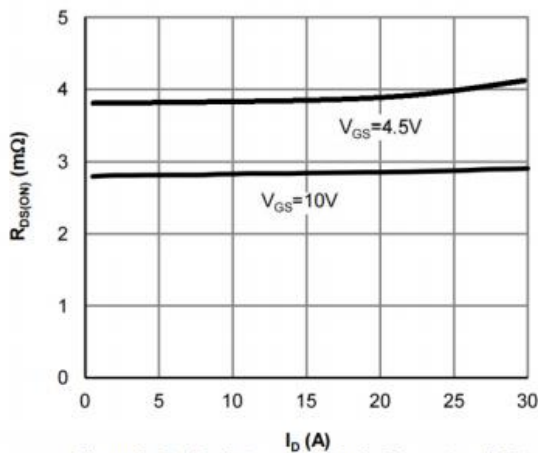


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

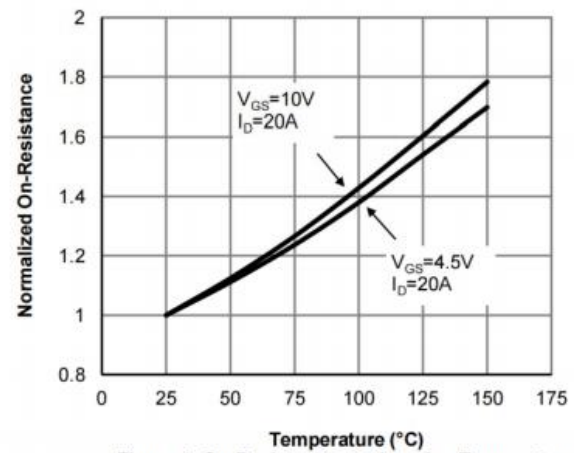


Figure 4: On-Resistance vs. Junction Temperature

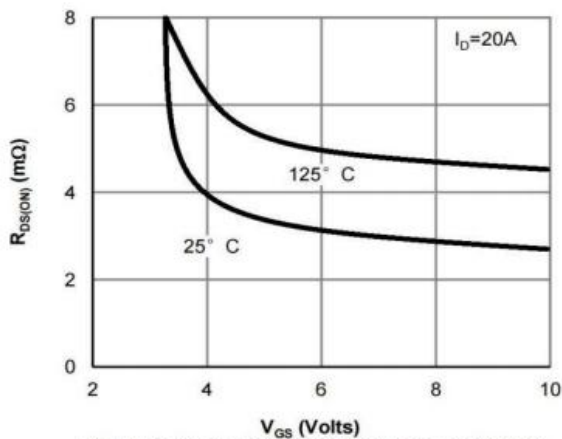


Figure 5: On-Resistance vs. Gate-Source Voltage

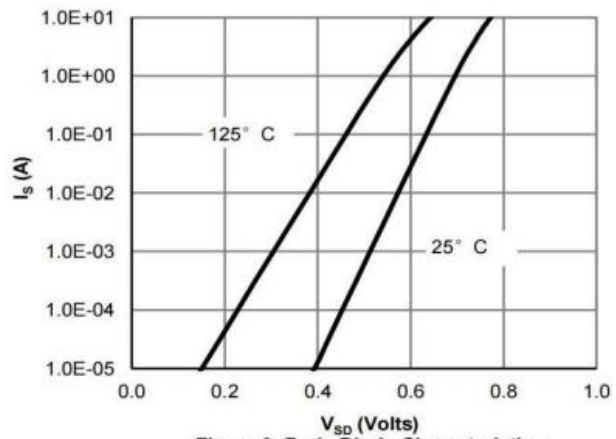


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve

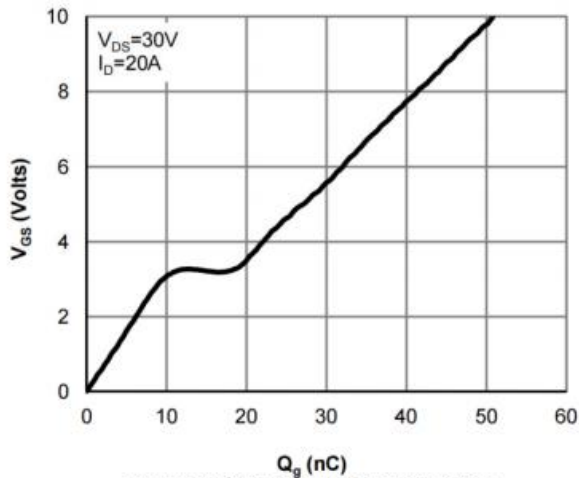


Figure 7: Gate-Charge Characteristics

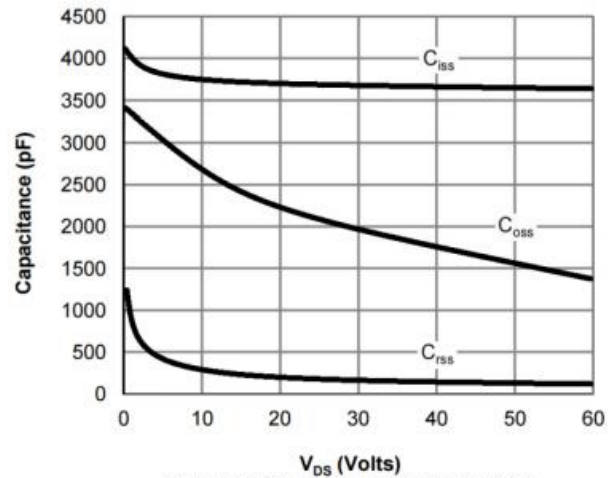


Figure 8: Capacitance Characteristics

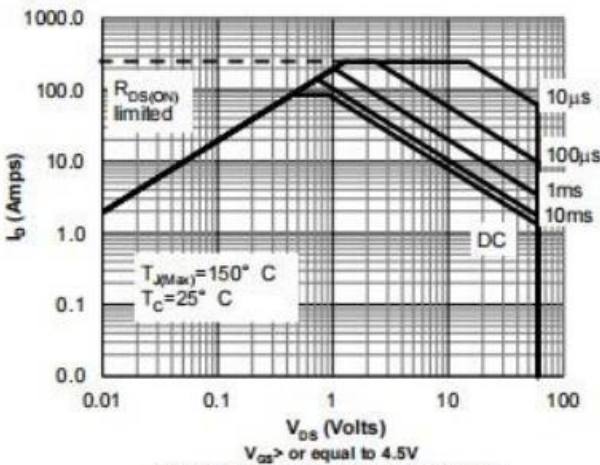


Figure 9: Maximum Forward Biased Safe Operating Area

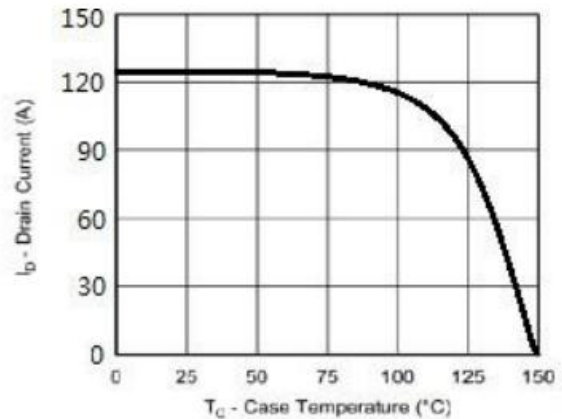


Figure 10: Maximum Continuous Drain Current vs Case Temperature

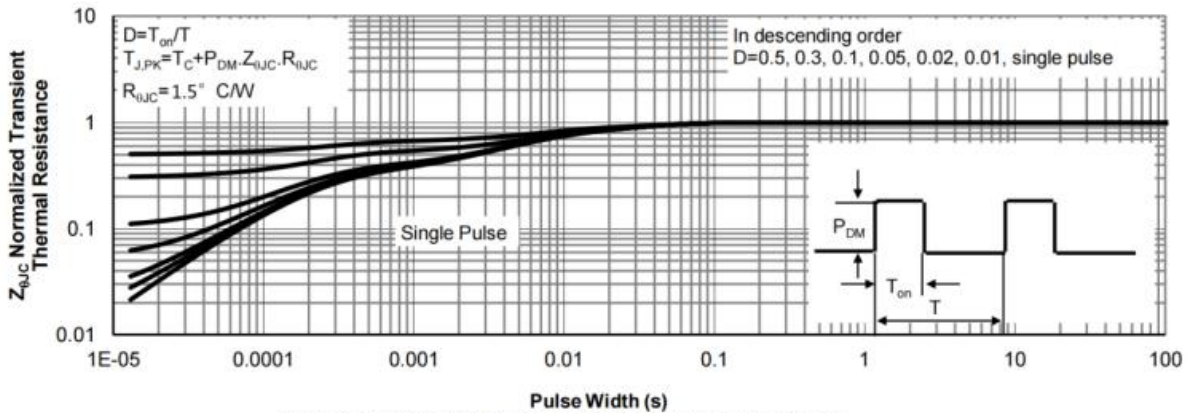
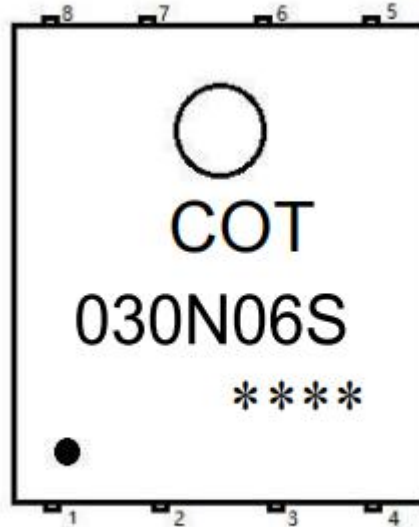


Figure 11: Normalized Maximum Transient Thermal Impedance

**Marking Instructions**



Note:

COT: Company Code.

030N06S: Product Type Code.

\*\*\*\*: Lot No. Code, code change with Lot No.

**Packaging SPEC**

REEL INFORMATION

Package Type	Units					Dimension (unit: mm <sup>3</sup> )		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
PDFN5×6	5000	2	10000	6	60000	13"×12	360×360×50	380×335×366

**Package Outline Dimensions**

**PDFN5×6 外形尺寸图**

PDFN5 X6

Unit:mm

